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|  | <p>SI2325DS-T1-GE3</p> |
| | <p>Hersteller-Teilenummer: SI2325DS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 150V 0.53A SOT-23</p> <p>Datenblätter:  SI2325DS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 39238 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

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| Teilenummer | SI2325DS-T1-GE3 |
| Hersteller | Vishay / Siliconix |
| Beschreibung | MOSFET P-CH 150V 0.53A SOT-23 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 39238 pcs Stock |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | TO-236-3, SC-59, SOT-23-3 |
| Supplier Device-Gehäuse | SOT-23-3 (TO-236) |
| Verlustleistung (max) | 750mW (Ta) |
| Typ FET | P-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 150V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 530mA (Ta) |
| Rds On (Max) @ Id, Vgs | 1.2 Ohm @ 500mA, 10V |
| VGS (th) (Max) @ Id | 4.5V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 12nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | 510pF @ 25V |
| Antriebsspannung (Max Rds On, Min Rds On) | 6V, 10V |
| Vgs (Max) | ±20V |
| Verpackung | Tape & Reel (TR) |

SI2325DS-T1-GE3 ist neu im Original, Suche SI2325DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2325DS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2325DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

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|---|--|---|--|
|  <p>SI2324DS-T1-GE3 Vishay / Siliconix MOSFET N-CH 100V 2.3A SOT-23</p> |  <p>SI2327DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 200V 0.38A SOT-23</p> |  <p>SI2325DS-T1-E3 Vishay / Siliconix MOSFET P-CH 150V 0.53A SOT23-3</p> |  <p>SI2325DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 150V 0.53A SOT23-3</p> |
|  <p>SI2324DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 2.3A SOT-23</p> |  <p>SI2326DS-T1-E3 VISHAY VISHAY SOT23</p> |  <p>SI2327DS-T1-E3 Vishay / Siliconix MOSFET P-CH 200V 0.38A SOT23-3</p> |  <p>SI2326DS-T1-GE3 VISHAY VISHAY SOT23</p> |

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|  SI2320DS |  SI2320DS-T1-E3 |  SI2320DS-T1-GE3 |  SI2321DS-T1-E3 |  SI2321DS-T1-E3 |
|  SI2321DS-T1-GE3 |  SI2321DS-T1-GE3 |  SI2323CDS-T1 |  SI2323CDS-T1-E3 |  SI2323CDS-T1-GE3 |
|  SI2323CDS-T1-GE3 |  SI2323DDS-T1-E3 |  SI2323DDS-T1-GE3 |  SI2323DDS-T1-GE3 |  SI2323DS |
|  SI2323DS-T1-E3 |  SI2323DS-T1-E3 |  SI2323DS-T1-GE3 |  SI2323DS-T1-GE3 |  SI2324DS-T1-E3 |
|  SI2324DS-T1-GE3 |  SI2324DS-T1-GE3 |  SI2325DS-T1-E3 |  SI2325DS-T1-E3 |  SI2325DS-T1-GE3 |
|  SI2327DS-T1-E3 |  SI2327DS-T1-E3 |  SI2327DS-T1-GE3 |  SI2327DS-T1-GE3 |  SI2328DS |
|  SI2328DS-T1 |  SI2328DS-T1-E3 |  SI2328DS-T1-E3 |  SI2328DS-T1-GE3 |  SI2328DS-T1-GE3 |
|  SI2329DS-T1-E3 |  SI2329DS-T1-GE3 |  SI2329DS-T1-GE3 |  SI2331DS |  SI2331DS-T1-E3 |
|  SI2331DS-T1-E3 |  SI2331DS-T1-GE3 |  SI2331DS-T1-GE3 |  SI2333ADS-T1-GE3 |  SI2333CDS |
|  SI2333CDS-T1-E3 |  SI2333CDS-T1-E3 |  SI2333CDS-T1-GE3 |  SI2333CDS-T1-GE3 |  SI2333DDS-T1-E3 |

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